



# ACE12334M

## P-Channel 20-V (D-S) MOSFET

### Features

- Low  $r_{DS(on)}$  trench technology
- Low thermal impedance
- Fast switching speed

### Applications

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

Product Summary		
$V_{DS}$ (V)	$r_{DS(on)}$ (m $\Omega$ )	$I_D$ (A)
-20	42 @ $V_{GS} = -4.5V$	-5.7
	57 @ $V_{GS} = -2.5V$	-4.9
	80 @ $V_{GS} = -1.8V$	-4.1

### Absolute Maximum Ratings

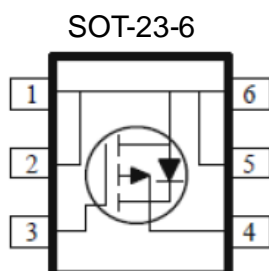
Parameter	Symbol	Limit	Units
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	$\pm 8$	V
Continuous Drain Current	$I_D$	$T_A=25^\circ C$	-5.7
		$T_A=70^\circ C$	-4.6
Pulse Drain Current <sup>a</sup>	$I_{DM}$	-20	A
Continuous Drain Current (Diode Continuous)	$I_S$	-2.5	A
Power Dissipation <sup>a</sup>	$P_D$	$T_A=25^\circ C$	2
		$T_A=70^\circ C$	1.3
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ C$

Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient <sup>a</sup>	$R_{\theta JA}$	t $\leq$ 10 sec	62.5
		Steady State	110

### Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

### Packaging Type



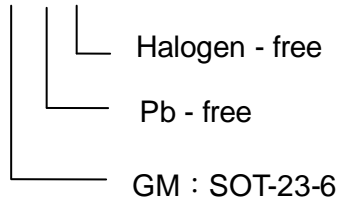


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### Ordering information

ACE12334M XX + H



### Electrical Characteristics

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Source Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.4			V
Gate Body Leakage	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 8V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-16V, V_{GS}=0V$			-1	uA
		$V_{DS}=-16V, V_{GS}=0V, T_J=55^\circ C$			-25	
On-State Drain-Current <sup>a</sup>	$I_{D(on)}$	$V_{DS}=-5V, V_{GS}=-4.5V$	-8.55			A
Static Drain-Source On-Resistance <sup>a</sup>	$r_{DS(ON)}$	$V_{GS}=-4.5V, I_D=-4.6A$			42	mΩ
		$V_{GS}=-2.5V, I_D=-3.7A$			57	
		$V_{GS}=-1.8V, I_D=-3A$			80	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS}=-15V, I_D=-4.6A$		12		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S=-1.3A, V_{GS}=0V$		-0.78		V
Dynamic <sup>b</sup>						
Total Gate Charge	$Q_g$	$V_{DS}=-10V, V_{GS}=-4.5V, I_D=-4.6A$		10		nC
Gate-Source Charge	$Q_{gs}$			1.8		
Gate-Drain Charge	$Q_{gd}$			3.1		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS}=-10V, R_L=2.2\Omega, I_D=-4.6A, V_{GEN}=-4.5V, R_{GEN}=6\Omega$		10		ns
Rise Time	$t_r$			12		
Turn-Off Delay Time	$t_{d(off)}$			42		
Fall Time	$t_f$			19		
Input Capacitance	$C_{iss}$	$V_{DS}=-15V, V_{GS}=0V, f=1MHz$		666		pF
Output Capacitance	$C_{oss}$			88		
Reverse Transfer Capacitance	$C_{rss}$			80		

Note:

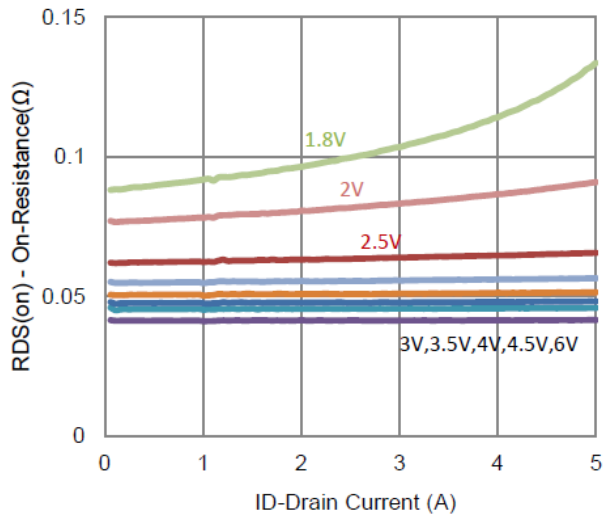
- a. Pulse test: PW ≤ 300us duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.



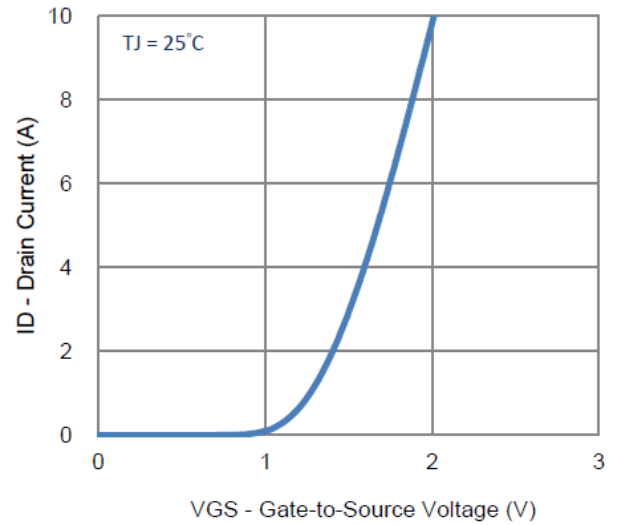
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## P-Channel 20-V (D-S) MOSFET

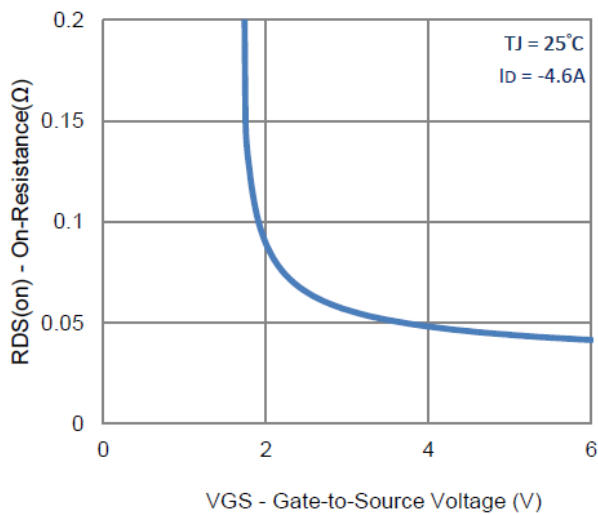
### Typical Electrical Characteristics



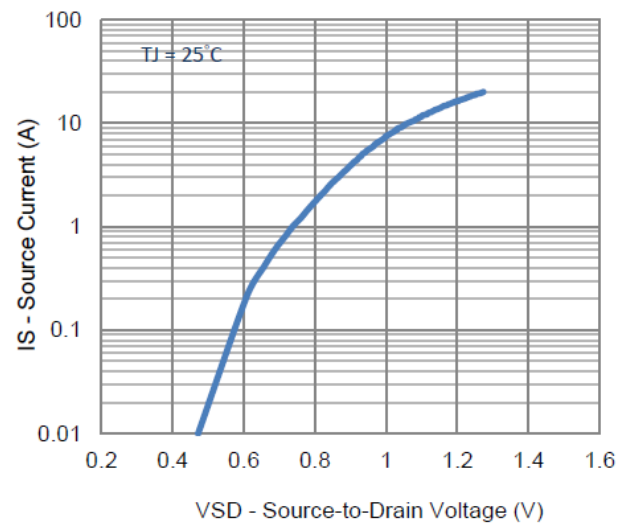
**1. On-Resistance vs. Drain Current**



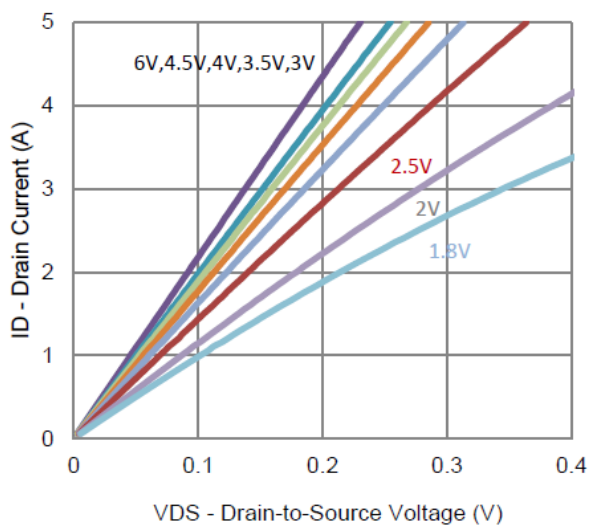
**2. Transfer Characteristics**



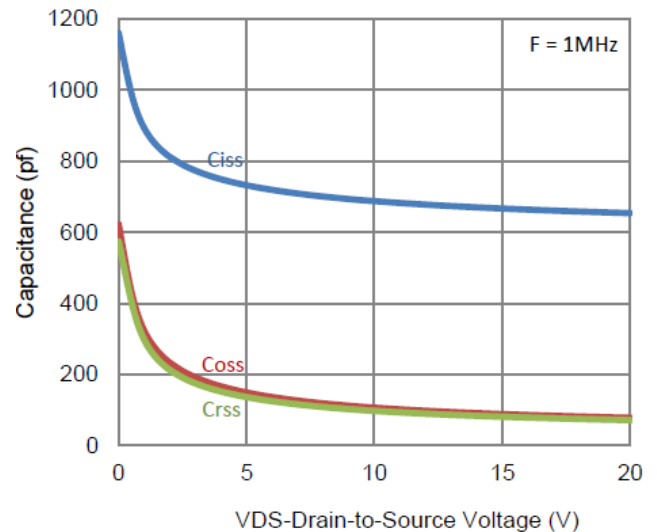
**3. On-Resistance vs. Gate-to-Source Voltage**



**4. Drain-to-Source Forward Voltage**



**5. Output Characteristics**

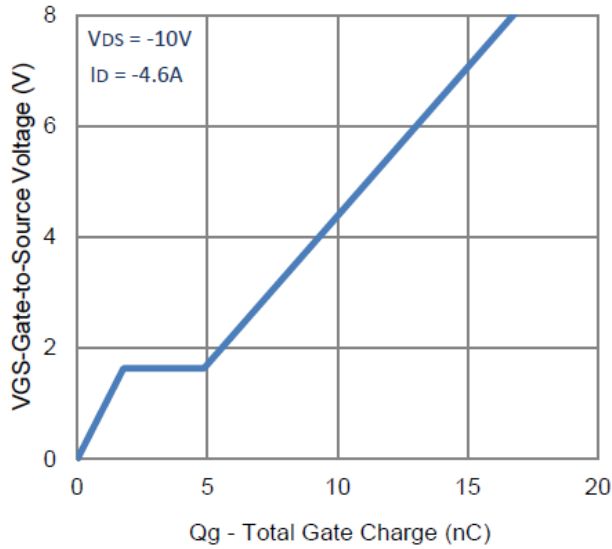


**6. Capacitance**

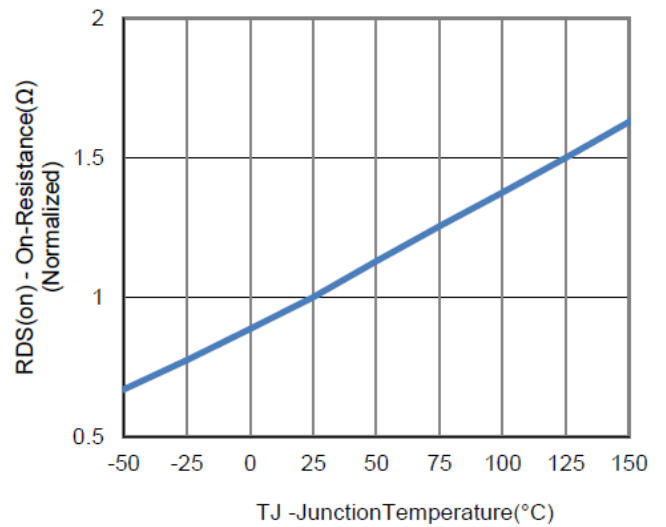


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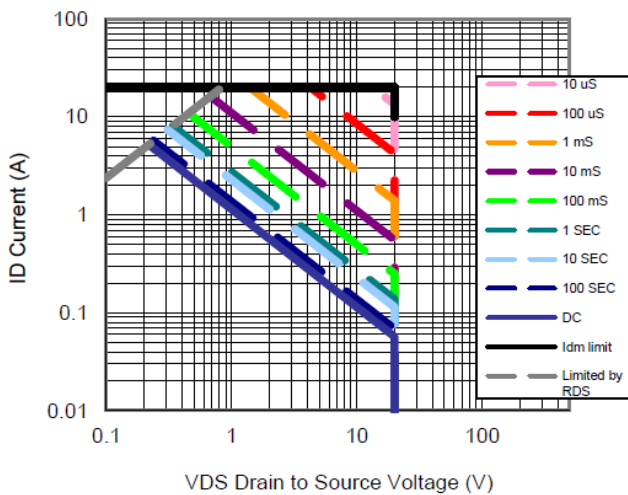
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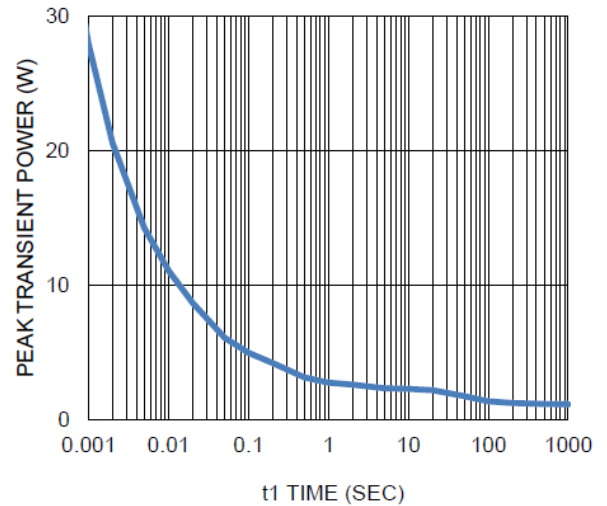
7. Gate Charge



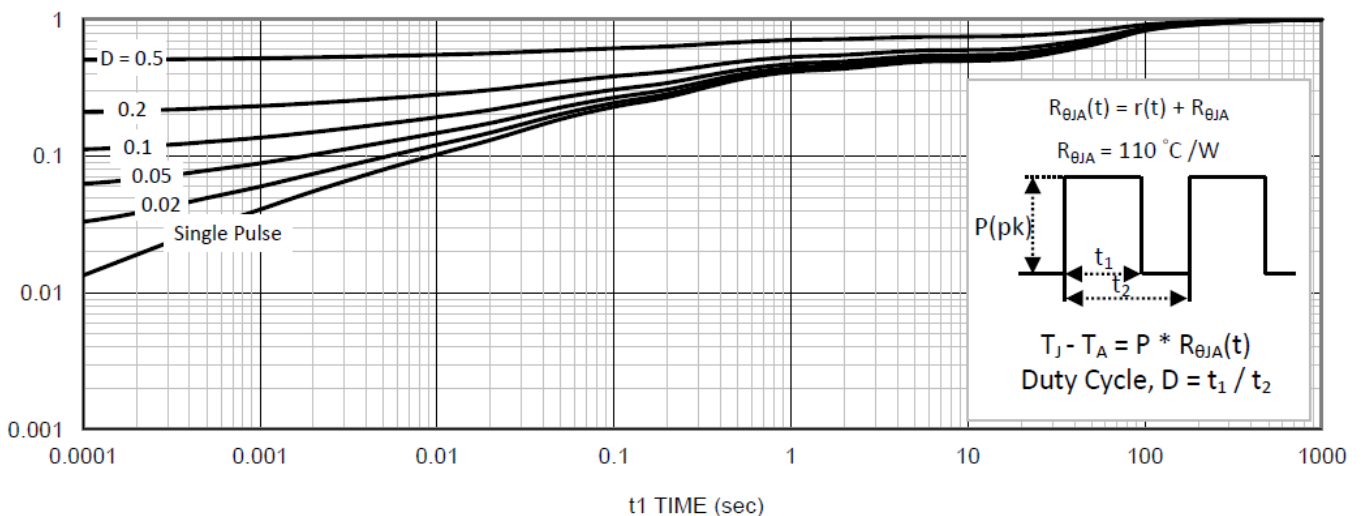
8. Normalized On-Resistance Vs Junction Temperature



9. Safe Operating Area



10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

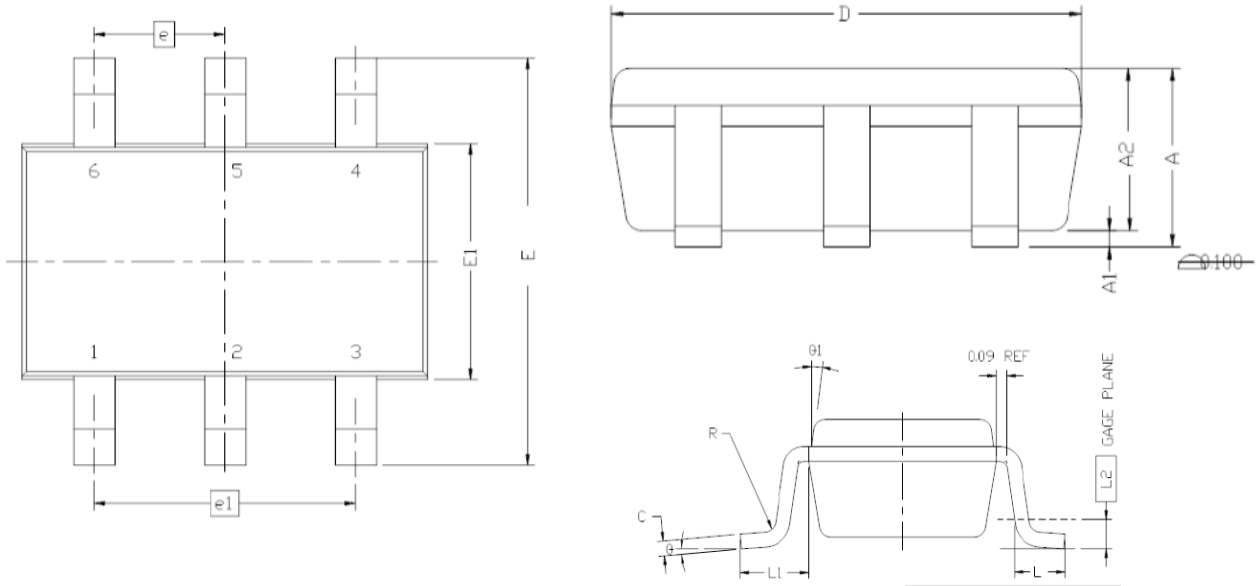


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## P-Channel 20-V (D-S) MOSFET

### Packing Information

SOT-23-6



SYMBOLS	DIMENSIONS IN MILLIMETERS		
	MIN	NOM	MAX
A	0.80	0.95	1.00
A1	0.00		0.10
A2	0.70	0.875	0.90
b	0.35	0.40	0.50
b2	0.10	0.127	0.20
c	2.90 BSC		
c2	2.80 BSC		
D	1.60 BSC		
D1	0.95 BSC		
D2	1.90 BSC		
E	0.30	0.40	0.60
E1	0.60 REF		
e	0.254 BSC		
H	0.10		
L3	0°	4°	8°
θ	7° NOM		



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### Notes

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1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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